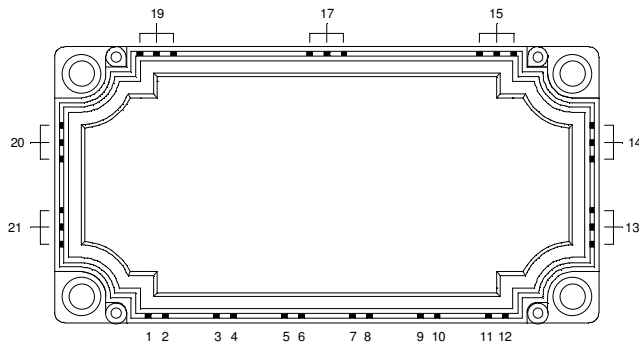
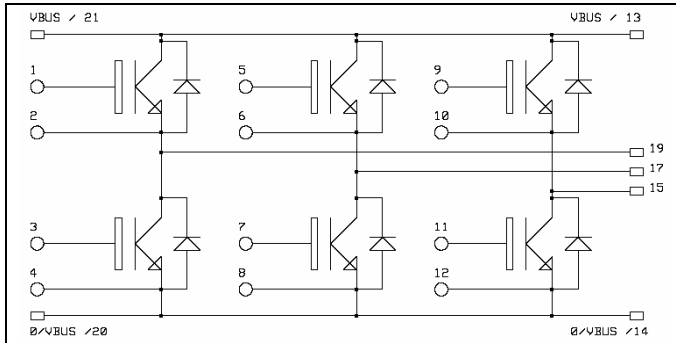


3 Phase bridge Trench IGBT® Power Module

$V_{CES} = 1200V$
 $I_C = 150A @ T_c = 80^\circ C$



Application

- AC Motor control

Features


- Trench + Field Stop IGBT® Technology
 - Low voltage drop
 - Low tail current
 - Switching frequency up to 20 kHz
 - Soft recovery parallel diodes
 - Low diode VF
 - Low leakage current
 - Avalanche energy rated
 - RBSOA and SCSOA rated
- Kelvin emitter for easy drive
- Very low stray inductance
- High level of integration

Benefits

- Stable temperature behavior
- Very rugged
- Solderable terminals for easy PCB mounting
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Easy paralleling due to positive TC of VCEsat
- Low profile

Absolute maximum ratings

Symbol	Parameter	Max ratings	Unit
V_{CES}	Collector - Emitter Breakdown Voltage	1200	V
I_C	Continuous Collector Current	$T_C = 25^\circ C$	220
		$T_C = 80^\circ C$	150
I_{CM}	Pulsed Collector Current	$T_C = 25^\circ C$	350
V_{GE}	Gate - Emitter Voltage	± 20	V
P_D	Maximum Power Dissipation	$T_C = 25^\circ C$	700
SCSOA	Short Circuit Safe Operating Area	$T_j = 125^\circ C$	600A@900V

 **CAUTION:** These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed.

All ratings @ $T_j = 25^\circ\text{C}$ unless otherwise specified

Electrical Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
BV_{CES}	Collector - Emitter Breakdown Voltage	$V_{GE} = 0V, I_C = 6mA$	1200			V
I_{CES}	Zero Gate Voltage Collector Current	$V_{GE} = 0V, V_{CE} = 1200V$			4	mA
$V_{CE(on)}$	Collector Emitter on Voltage	$V_{GE} = 15V$ $I_C = 150A$		$T_j = 25^\circ\text{C}$ $T_j = 125^\circ\text{C}$	1.7 2.1	V
$V_{GE(th)}$	Gate Threshold Voltage	$V_{GE} = V_{CE}, I_C = 6mA$	5.0	5.8	6.5	V
I_{GES}	Gate - Emitter Leakage Current	$V_{GE} = 20V, V_{CE} = 0V$			600	nA

Dynamic Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
C_{ies}	Input Capacitance	$V_{GE} = 0V$		10.8		nF
C_{oes}	Output Capacitance	$V_{CE} = 25V$		0.56		
C_{res}	Reverse Transfer Capacitance	$f = 1MHz$		0.5		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (25°C)		250		ns
T_r	Rise Time	$V_{GE} = \pm 15V$		30		
$T_{d(off)}$	Turn-off Delay Time	$V_{Bus} = 600V$ $I_C = 150A$		420		
T_f	Fall Time	$R_G = 2.2\Omega$		70		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (125°C)		300		ns
T_r	Rise Time	$V_{GE} = \pm 15V$		50		
$T_{d(off)}$	Turn-off Delay Time	$V_{Bus} = 600V$ $I_C = 150A$		520		
T_f	Fall Time	$R_G = 2.2\Omega$		90		

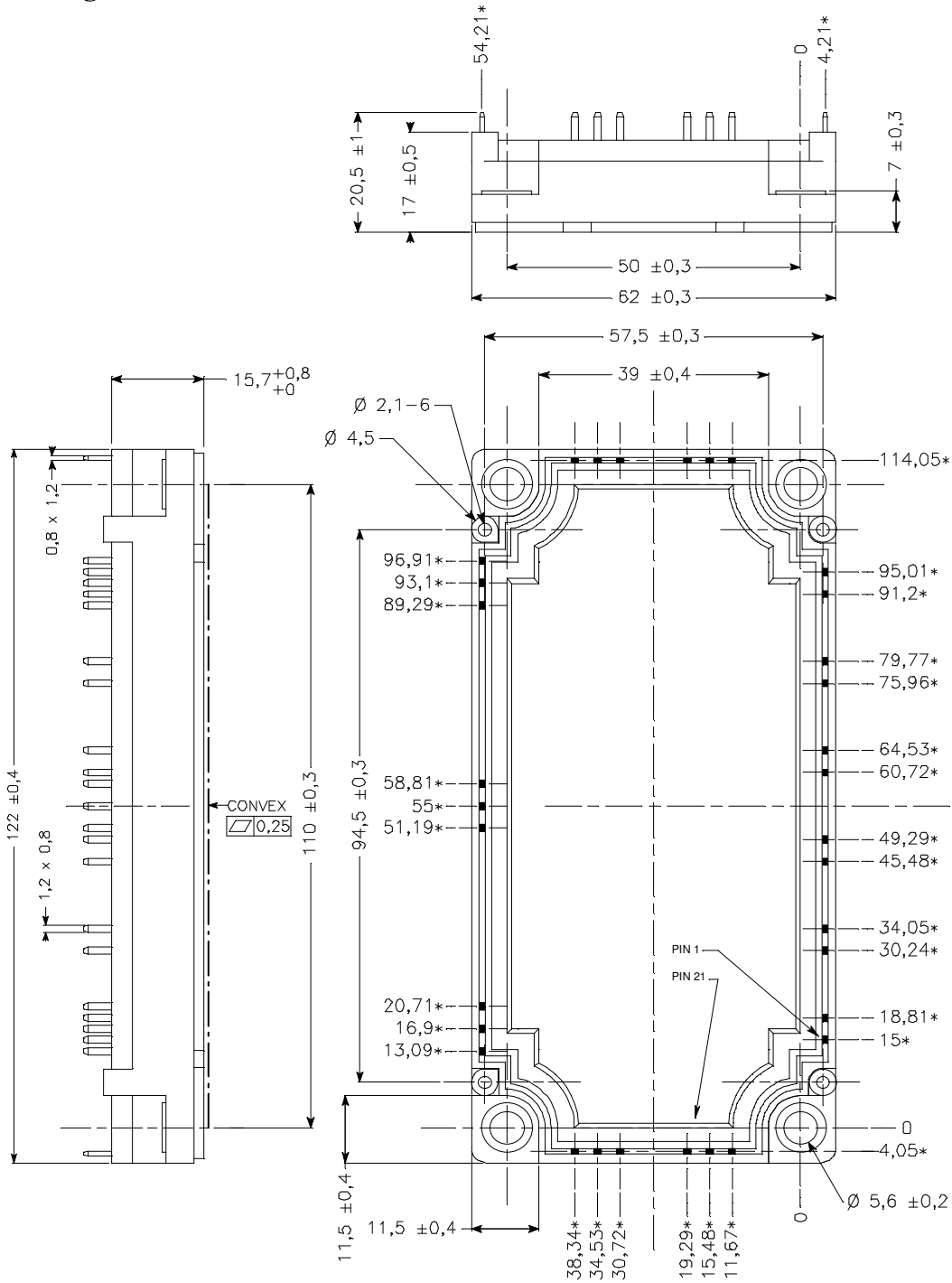
Reverse diode ratings and characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
V_F	Diode Forward Voltage	$I_F = 150A$ $V_{GE} = 0V$		$T_j = 25^\circ\text{C}$ $T_j = 125^\circ\text{C}$	1.6 1.6	2.1 V
E_{rec}	Reverse Recovery Energy	$I_F = 150A$ $V_R = 600V$ $di/dt = 900A/\mu s$		$T_j = 125^\circ\text{C}$	12	mJ
Q_{rr}	Reverse Recovery Charge	$I_F = 150A$ $V_R = 600V$ $di/dt = 900A/\mu s$		$T_j = 25^\circ\text{C}$ $T_j = 125^\circ\text{C}$	14 28	μC

Thermal and package characteristics

Symbol	Characteristic	Min	Typ	Max	Unit	
R_{thJC}	Junction to Case	IGBT		0.18	$^\circ\text{C/W}$	
		Diode		0.30		
V_{ISOL}	RMS Isolation Voltage, any terminal to case $t = 1$ min, $I_{isol} < 1mA, 50/60Hz$	2500			V	
T_j	Operating junction temperature range	-40		150	$^\circ\text{C}$	
T_{STG}	Storage Temperature Range	-40		125		
T_C	Operating Case Temperature	-40		125		
Torque	Mounting torque	To Heatsink	M5	3		4.5
Wt	Package Weight				300	g

Package outline



ALL DIMENSIONS MARKED "*" ARE TOLERENCED AS: $\text{⌀} \pm 0,4$

APT reserves the right to change, without notice, the specifications and information contained herein

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